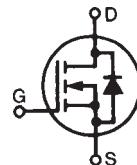


**Polar2™ HiperFET™
Power MOSFET**

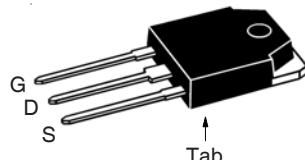
IXFQ24N50P2

**V_{DSS} = 500V
 I_{D25} = 24A
 $R_{DS(on)}$ ≤ 270mΩ**

N-Channel Enhancement Mode
 Avalanche Rated
 Fast Intrinsic Diode



TO-3P



G = Gate D = Drain
 S = Source Tab = Drain

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	500	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C , $R_{GS} = 1\text{M}\Omega$	500	V
V_{GSS}	Continuous	± 30	V
V_{GSM}	Transient	± 40	V
I_{D25}	$T_C = 25^\circ\text{C}$	24	A
I_{DM}	$T_C = 25^\circ\text{C}$, Pulse Width Limited by T_{JM}	50	A
I_A	$T_C = 25^\circ\text{C}$	12	A
E_{AS}	$T_C = 25^\circ\text{C}$	750	mJ
dv/dt	$I_S \leq I_{DM}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$	15	V/ns
P_D	$T_C = 25^\circ\text{C}$	480	W
T_J		-55 ... +150	°C
T_{JM}		150	°C
T_{stg}		-55 ... +150	°C
T_L	Maximum Lead Temperature for Soldering	300	°C
T_{SOLD}	Plastic Body for 10s	260	°C
M_d	Mounting Torque	1.13/10	Nm/lb.in.
Weight		5.5	g

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0\text{V}$, $I_D = 250\mu\text{A}$	500		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 1\text{mA}$	2.5		4.5 V
I_{GSS}	$V_{GS} = \pm 30\text{V}$, $V_{DS} = 0\text{V}$			± 100 nA
I_{DSS}	$V_{DS} = V_{DSS}$, $V_{GS} = 0\text{V}$ $T_J = 125^\circ\text{C}$			25 μA 1 mA
$R_{DS(on)}$	$V_{GS} = 10\text{V}$, $I_D = 0.5 \cdot I_{D25}$, Note 1			270 mΩ

Features

- Fast Intrinsic Diode
- Dynamic dv/dt Rating
- Avalanche Rated
- Low $R_{DS(ON)}$ and Q_G
- Low Package Inductance

Advantages

- High Power Density
- Easy to Mount
- Space Savings

Applications

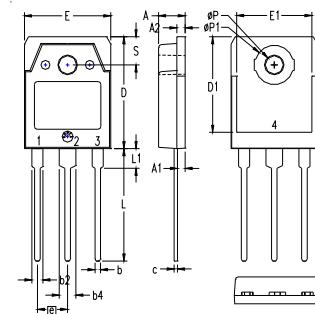
- Switch-Mode and Resonant-Mode Power Supplies
- DC-DC Converters
- Battery Chargers
- Uninterrupted Power Supplies
- AC and DC Motor Drives
- High Speed Power Switching Application

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)		Characteristic Values		
			Min.	Typ.	Max.
g_{fs}	$V_{DS} = 20\text{V}$, $I_D = 0.5 \cdot I_{D25}$, Note 1	14	24	S	
C_{iss}		2890		pF	
C_{oss}	$V_{GS} = 0\text{V}$, $V_{DS} = 25\text{V}$, $f = 1\text{MHz}$	280		pF	
C_{rss}		22		pF	
$t_{d(on)}$	Resistive Switching Times $V_{GS} = 10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 0.5 \cdot I_{D25}$ $R_G = 10\Omega$ (External)	15		ns	
t_r		9		ns	
$t_{d(off)}$		30		ns	
t_f		5		ns	
$Q_{g(on)}$		48		nC	
Q_{gs}	$V_{GS} = 10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 0.5 \cdot I_{D25}$	13		nC	
Q_{gd}		16		nC	
R_{thJC}			0.26	$^\circ\text{C}/\text{W}$	
R_{thCS}		0.25		$^\circ\text{C}/\text{W}$	

Source-Drain Diode

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)		Characteristic Values		
			Min.	Typ.	Max.
I_s	$V_{GS} = 0\text{V}$			24	A
I_{SM}	Repetitive, Pulse Width Limited by T_{JM}			96	A
V_{SD}	$I_F = I_S$, $V_{GS} = 0\text{V}$, Note 1			1.3	V
t_{rr}	$I_F = 12\text{A}$, $-di/dt = 100\text{A}/\mu\text{s}$ $V_R = 100\text{V}$, $V_{GS} = 0\text{V}$		200	ns	
I_{RM}		10		A	
Q_{RM}		0.69		μC	

Note 1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.

TO-3P (IXFQ) Outline

1 - GATE
2 - DRAIN (COLLECTOR)
3 - SOURCE (EMITTER)
4 - DRAIN (COLLECTOR)

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.185	.193	4.70	4.90
A1	.051	.059	1.30	1.50
A2	.057	.065	1.45	1.65
b	.035	.045	0.90	1.15
b2	.075	.087	1.90	2.20
b4	.114	.126	2.90	3.20
c	.022	.031	0.55	0.80
D	.780	.799	19.80	20.30
D1	.665	.677	16.90	17.20
E	.610	.622	15.50	15.80
E1	.531	.539	13.50	13.70
e	.215	BSC	5.45	BSC
L	.779	.795	19.80	20.20
L1	.134	.142	3.40	3.60
ϕP	.126	.134	3.20	3.40
$\phi P1$.272	.280	6.90	7.10
S	.193	.201	4.90	5.10

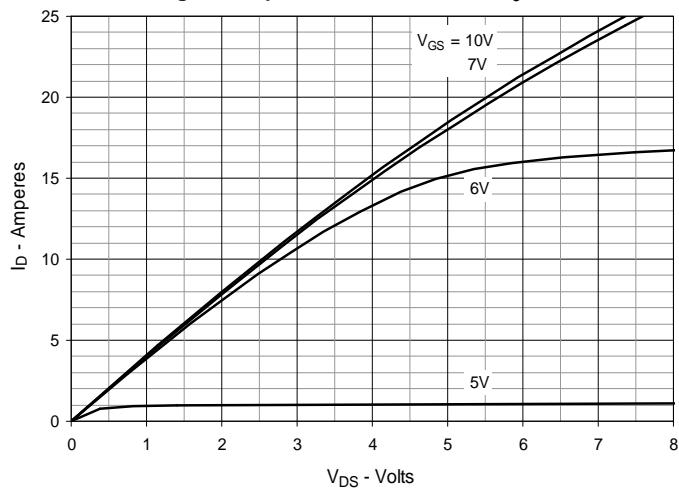
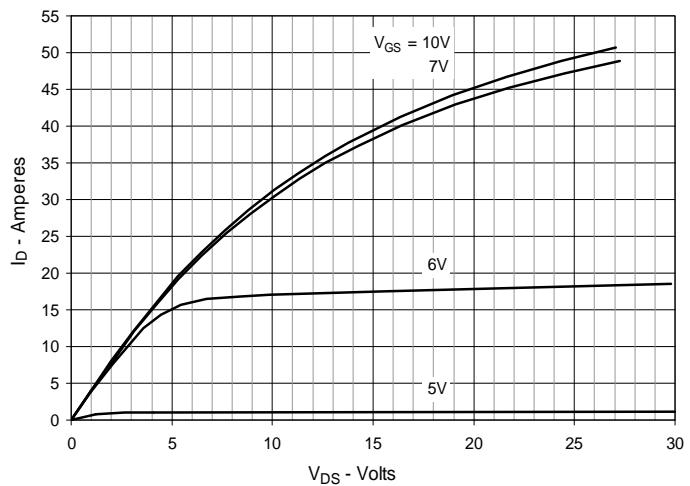
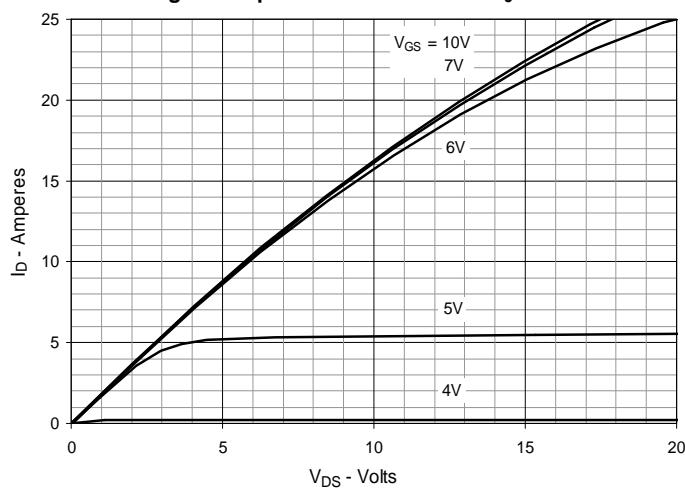
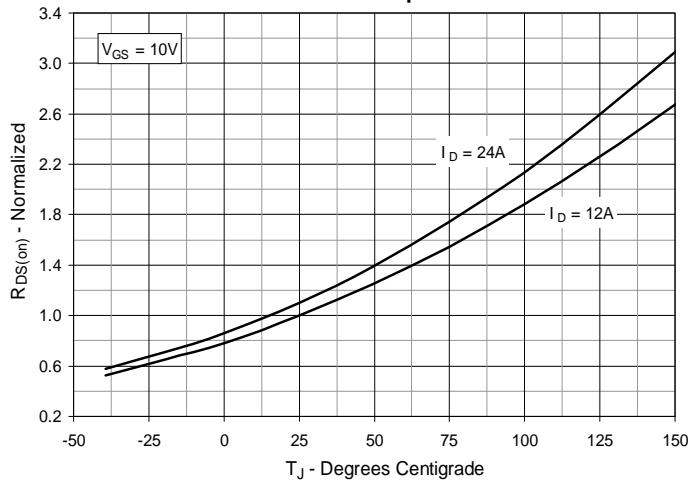
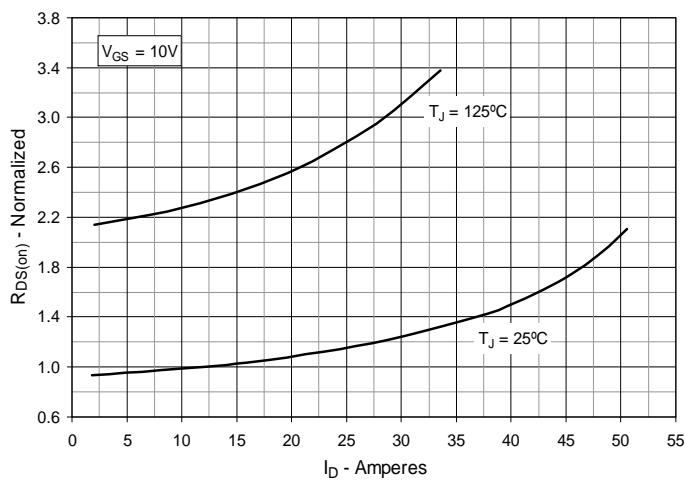
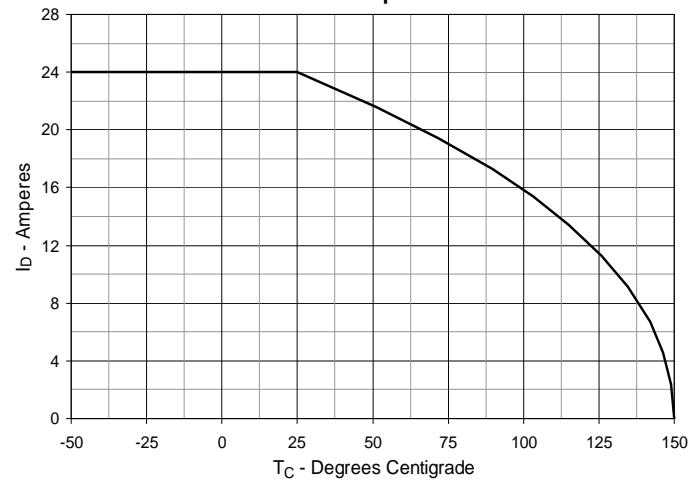
Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$ **Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$** **Fig. 3. Output Characteristics @ $T_J = 125^\circ\text{C}$** **Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 12\text{A}$ Value vs. Junction Temperature****Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 12\text{A}$ Value vs. Drain Current****Fig. 6. Maximum Drain Current vs. Case Temperature**

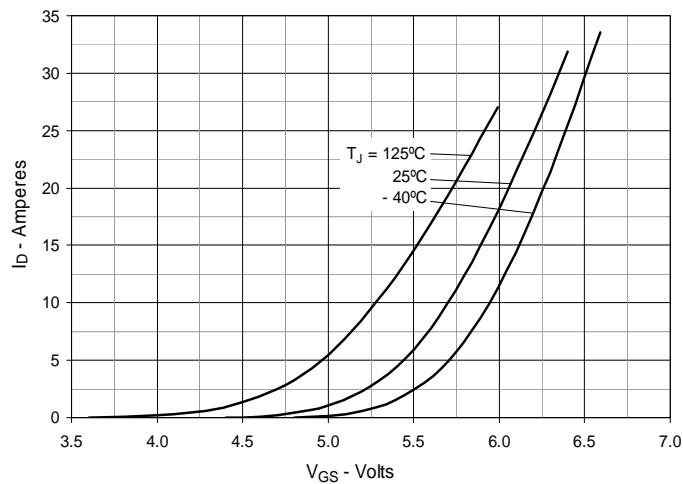
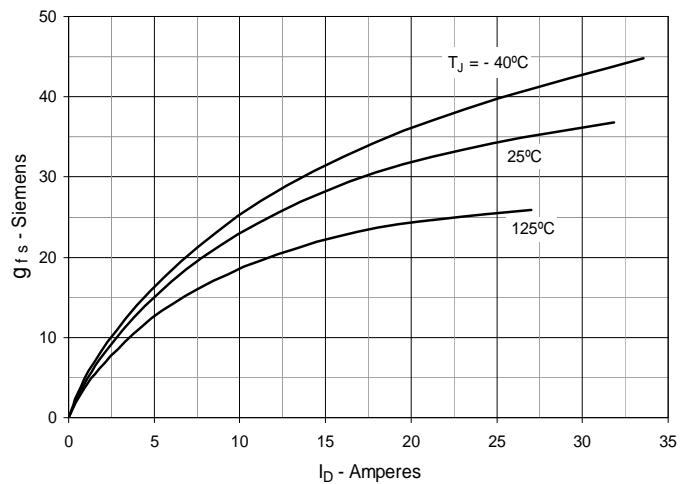
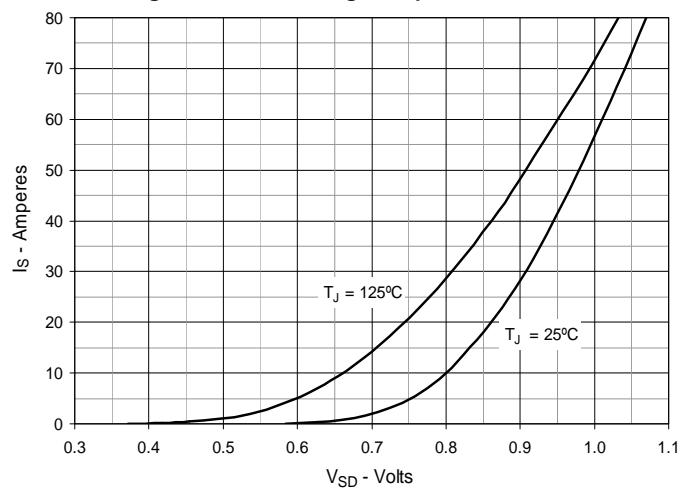
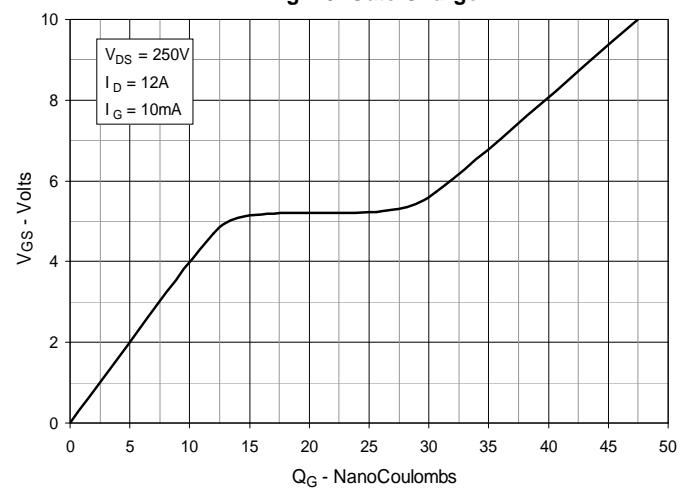
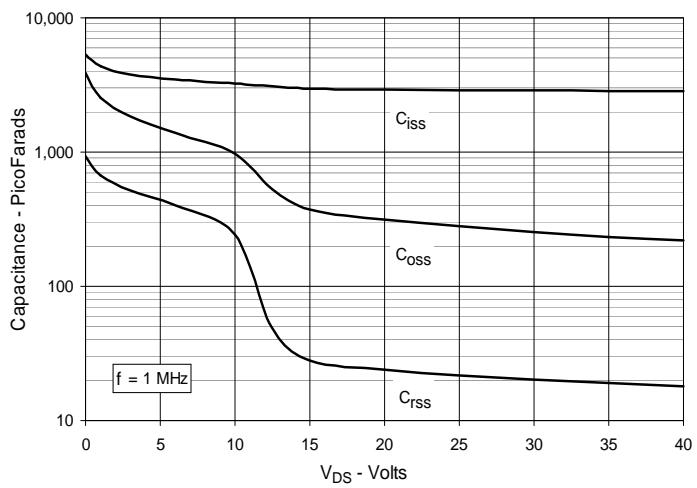
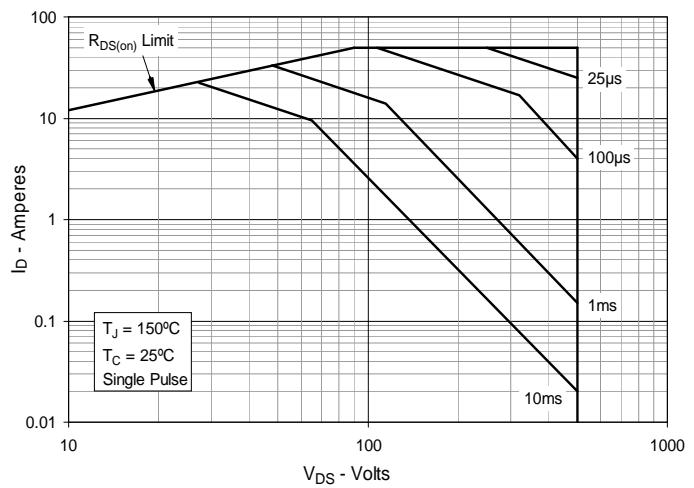
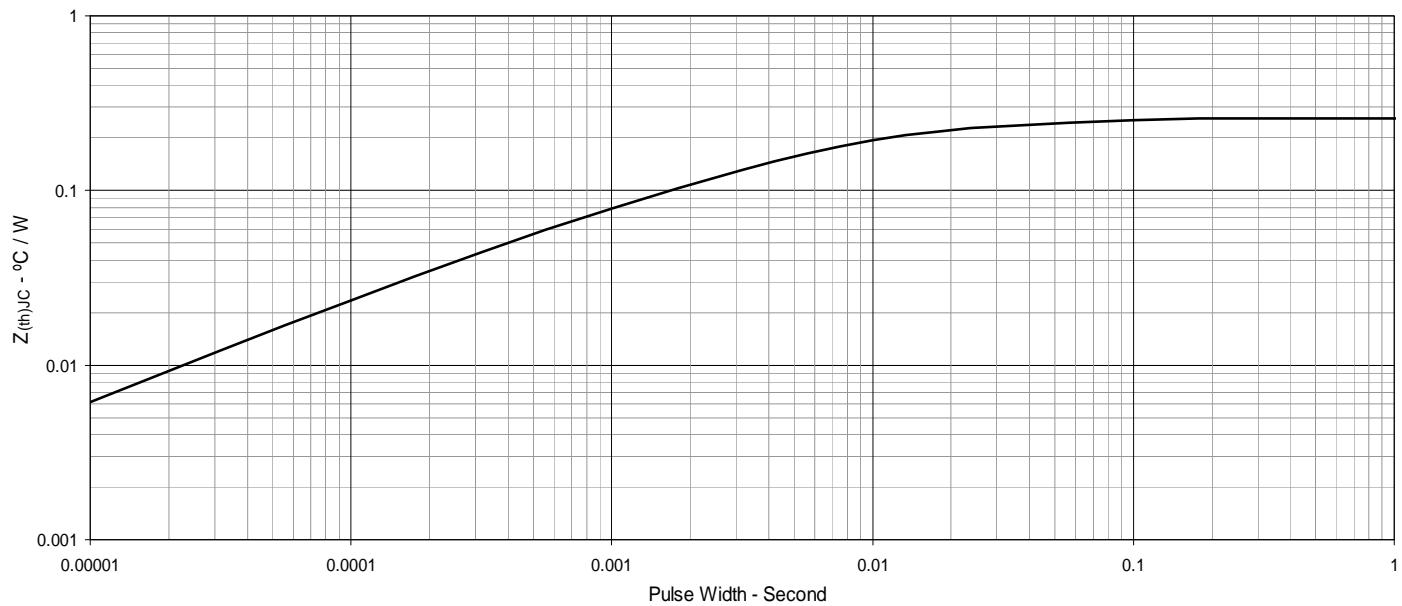
Fig. 7. Input Admittance**Fig. 8. Transconductance****Fig. 9. Forward Voltage Drop of Intrinsic Diode****Fig. 10. Gate Charge****Fig. 11. Capacitance****Fig. 12. Forward-Bias Safe Operating Area**

Fig. 13. Maximum Transient Thermal Impedance



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